

Features

- High isolation 3750 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- Operating Temperature range 55 °C to 110 °C
- Regulatory Approvals
 - UL UL1577 (E364000)
 - VDE EN60747-5-5(VDE0884-5)
 - CQC GB4943.1, GB8898
 - IEC60065, IEC60950
- Green Package

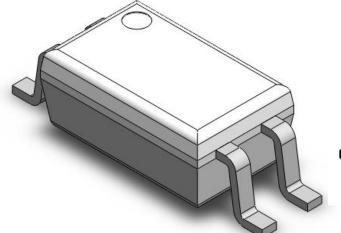
Description

The CTH214 series consists of a phototransistor optically coupled to two gallium arsenide Infrared-emitting diode, connected in inverse parallel in a 4-lead half pitch Mini-Flat package.

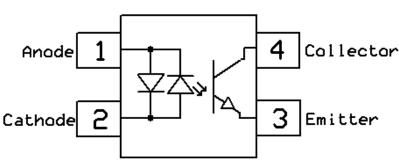
Applications

- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

Package Outline



Schematic





Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage	3750	V _{RMS}	
Ртот	Total power dissipation	200	mW	
Topr	Operating temperature	-55 ~ +110	°C	
Tstg	Storage temperature	-55 ~ + 150	°C	
TsoL	Soldering temperature	260	°C	
Emitter				
I _F	Forward current	±50	mA	
I _{F(TRANS)}	Peak transient current (≤1µs P.W,300pps)	1	Α	
P _D	Emitter power dissipation	70	mW	
Detector				
P _D	Detector power dissipation	150	mW	
Bvceo	Collector-Emitter Breakdown Voltage	80	V	
B _{VECO}	Emitter-Collector Breakdown Voltage	6	V	
Ic	Collector Current	50	mA	



Electrical Characteristics $T_A = 25$ °C (unless otherwise specified)

Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I _F =±10mA		1.24	1.4	V	
C _{IN}	Input Capacitance	f= 1MHz	-	30	-	pF	

Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
B _{VCEO}	Collector-Emitter Breakdown	Ic= 100μA	80	-	-	V	
Bveco	Emitter-Collector Breakdown	I _E = 100μA	6	-	-	V	
I _{CEO}	Collector-Emitter Dark Current	V _{CE} = 20V, I _F =0mA	-	-	100	nA	

Transfer Characteristics

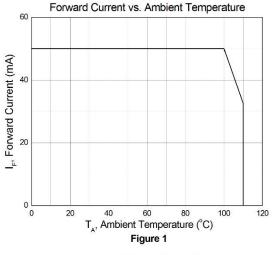
Symbol	Parameters		Test Conditions	Min	Тур	Max	Units	Notes
CTR	Current Transfer	CTH214	I _{F=} ±1mA, V _{CE} = 5V	20	ı	300	- %	
CIK	Ratio	CTH214A	F= ±IIIA, VCE= 5V	50	-	150	70	
CTR	Current Transfer	CTH214	I _{F=} ±5mA, V _{CE} = 5V	30		600	0/	
CIK	Ratio	CTH214A	F= ±SITIA, VCE= SV	80	-	300	%	
	CTR Symmetry		I _F = ±1mA, V _{CE} = 5V	0.7	-	1.3		
Vascaus	Collector-Emitter Saturation Voltage		I _F = ±20mA, I _C = 1mA	-	0.04	0.2	V	
V CE(SAT)			IF- 120IIIA, IC- IIIIA	-	0.04	0.2	V	
R _{IO}	Isolation Resistance		V _{IO} = 500V _{DC}	5x10 ¹⁰	•	-	Ω	
C _{IO}	Isolation Capacitance		f= 1MHz	-	0.5	1	pF	

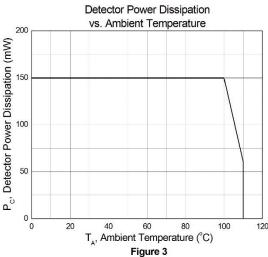
Switching Characteristics

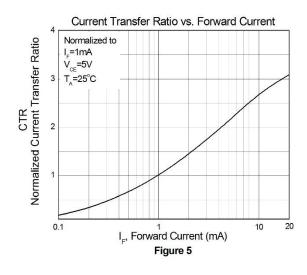
Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
t _r	Rise Time	L 077 A V 0V D 4000	-	6	-	0	
t _f	Fall Time	Ic= 2mA, V _{CE} = 2V, R _L = 100Ω	-	8	-	μS	

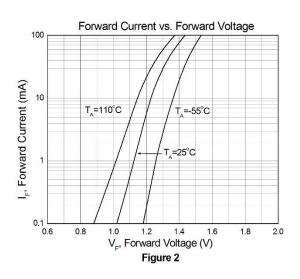


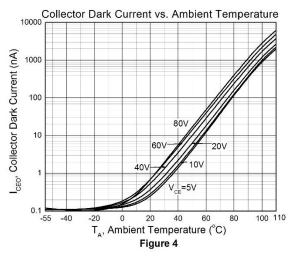
Typical Characteristic Curves

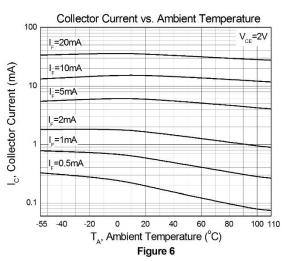




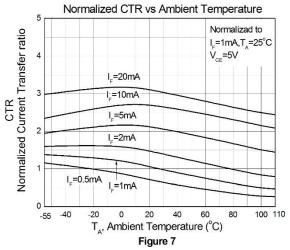


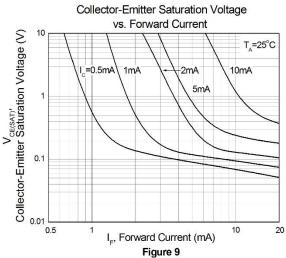


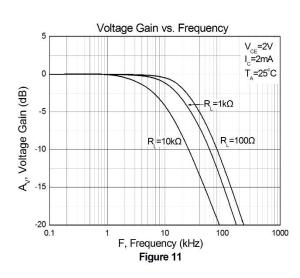


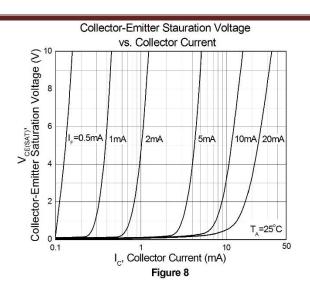


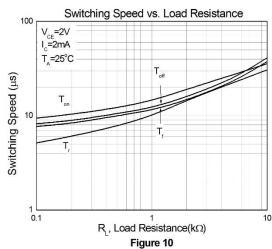


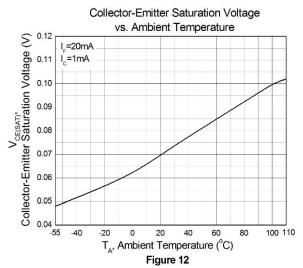






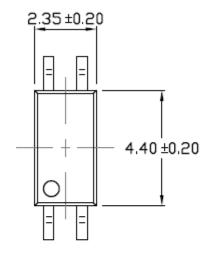


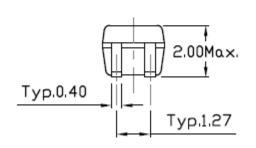


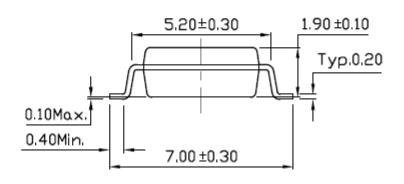




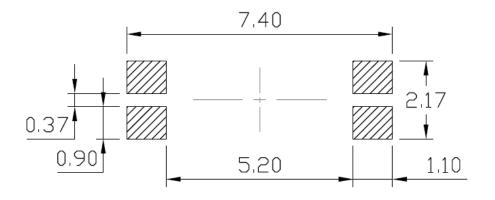
Package Dimension Dimensions in mm unless otherwise stated







Recommended Solder Mask Dimensions in mm unless otherwise stated





Marking Information



Note:

CT : Denotes "CT Micro" 214 : Product Number

R : CTR Rank
V : VDE Option
Y : Fiscal Year
WW : Work Week

K : Manufacturing Code

Ordering Information

CTH214X(V)(Z)

X = Part No. (X=A or none)

V = VDE Option (V or none)

Z = Tape and reel option (T1 or T2)

Option	Description	Quantity
T1	Surface Mount Lead Forming – With Option 1 Taping	5000 Units/Reel
T2	Surface Mount Lead Forming – With Option 2 Taping	5000 Units/Reel

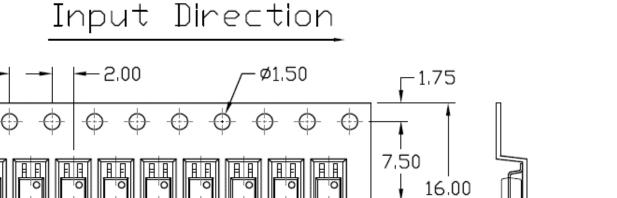


2.48

Carrier Tape Specifications Dimensions in mm unless otherwise stated

Option T1

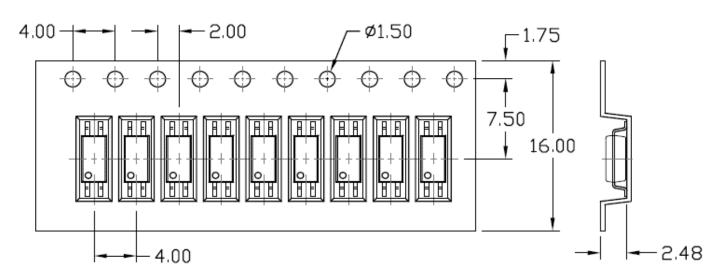
4,00-



Option T2

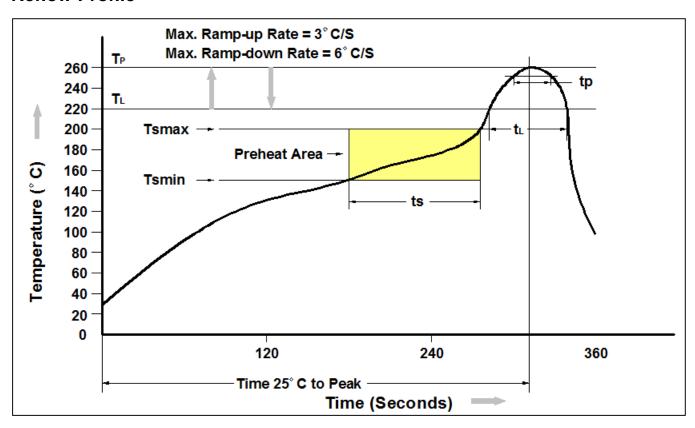
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Input Direction





Reflow Profile



Profile Feature	Pb-Free Assembly Profile			
Temperature Min. (Tsmin)	150°C			
Temperature Max. (Tsmax)	200°C			
Time (ts) from (Tsmin to Tsmax)	60-120 seconds			
Ramp-up Rate (t∟ to t _P)	3°C/second max.			
Liquidous Temperature (T _L)	217°C			
Time (t _L) Maintained Above (T _L)	60 – 150 seconds			
Peak Body Package Temperature	260°C +0°C / -5°C			
Time (t _P) within 5°C of 260°C	30 seconds			
Ramp-down Rate (T _P to T _L)	6°C/second max			
Time 25°C to Peak Temperature	8 minutes max.			



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单击下面可查看定价,库存,交付和生命周期等信息

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